| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|---|---|---|---|---|---|---|
| L14 | 21450 | (flatten$3 or planariz$3 or smooth$3) same wafer | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/08 08:22 |
| L15 | 600 | 14 same ((remov$3 or etch$3) same (silicon near oxide)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/08 08:23 |
| L16 | 129 | 15 same (expos$3 same (silicon or wafer)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/08 08:24 |
| L17 | 0 | 16 and ((activat$3 same gas) same nozzle) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/08 08:24 |
| L18 | 15661 | ((local$2 or selective$2) same etch$3) same (silicon near oxide or "SiO.sub.2") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/08 09:11 |
| L19 | 79 | L18 same (nozzle same gas$4) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/08 08:35 |
| L20 | 75 | 19 and (mov$3 same nozzle) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/08 08:36 |
| L21 | 35 | 19 and ((mov$3 same nozzle) same (substrate or wafer)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/08 08:36 |
| L22 | 2085 | 18 same (mov$3 same substrate or wafer) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/08 08:38 |

| L23 | 0 | 18 same (mov$3 same (gas near (injector or ejector or nozzle))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/08 08:40 |
|---|---|---|---|---|---|---|
| L24 | 1 | 18 same (mov$3 same (injector or ejector or nozzle)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/08 08:41 |
| L25 | 1483 | (local$2 same etch$3) same (silicon near oxide or "SiO.sub.2") | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/08 08:58 |
| L26 | 15 | L25 and (spray$3 same gas$3) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/08 09:03 |
| L27 | 29 | (lateral$3 near mov$3) same (gas near (inject$3 or nozzle)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/08 09:04 |
| L28 | 55 | 18 and ((relat$3 near mov$3) same (substrate or wafer or gas near (inject$3 or nozzle))) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/08 09:13 |
| L29 | 16 | 28 and @pd<"20020722" | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/08 09:45 |
| L30 | 1092 | (ion near mill$3 or charged near particle near beam) same (etch$3 same silicon or silicon near oxide) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/08 09:46 |
| L31 | 0 | 30 same (relative near move$3) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/08 09:46 |
| L32 | 1 | 30 and (controll$3 same (relative near move$3)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/08 09:48 |

| L33 | 0 | 30 and (controll$3 same ((gas or ion or beam) same (eject$3 or nozzle) same mov$3)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/08 09:50 |
|-----|---|---|---|---|---|---|
| L34 | 0 | 30 and (controll$3 same (move$3 near nozzle)) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/08 09:51 |
| L35 | 54 | 30 and (controll$3 same move$3) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | OFF | 2005/10/08 09:51 |